

Product data sheet

## 1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a leadless ultra small DFN1608D-2 (SOD1608) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

## 2. Features and benefits

- Average forward current:  $I_{F(AV)} \le 2 A$
- Reverse voltage: V<sub>R</sub> ≤ 20 V
- Low forward voltage  $V_F \le 450 \text{ mV}$
- Low reverse current
- AEC-Q101 qualified
- Solderable side pads
- Package height typ. 0.37 mm
- Ultra small and leadless SMD plastic package

## 3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- LED backlight for mobile application
- Low power consumption applications
- Ultra high-speed switching
- Reverse polarity protection

## 4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
I <sub>F(AV)</sub>	average forward current	$\delta$ < 0.5; f = 20 kHz; T <sub>sp</sub> ≤ 130 °C; square wave		-	-	2	A
		δ < 0.5; f = 20 kHz; T <sub>amb</sub> ≤ 65 °C; square wave	[1]	-	-	2	A
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C		-	-	20	V
V <sub>F</sub>	forward voltage	$I_{F}$ = 2 A; pulsed; $t_{p}$ $\leq$ 300 $\mu s;$ $\delta$ $\leq$ 0.02; $T_{j}$ = 25 $^{\circ}C$		-	395	450	mV





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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
I <sub>R</sub>	reverse current	V <sub>R</sub> = 10 V; T <sub>j</sub> = 25 °C		-	70	350	μA
Dynamic characteristics							
t <sub>rr</sub>	reverse recovery time	$I_R = 0.5 \text{ A}; I_F = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 ^{\circ}\text{C}$		-	5	-	ns

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	к	cathode[1]		1 🛃 2
2	A	anode		sym001
			Transparent top view DFN1608D-2 (SOD1608)	

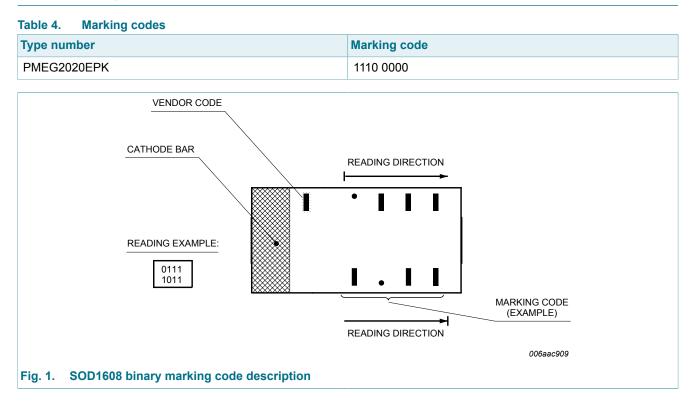
[1] The marking bar indicates the cathode.

## 6. Ordering information

Table 3.         Ordering information						
Type number	Package					
	Name	Description	Version			
PMEG2020EPK	DFN1608D-2	DFN1608D-2: leadless ultra small plastic package; 2 terminals	SOD1608			

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### 7. Marking



20 V, 2 A low VF MEGA Schottky barrier rectifier

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C		-	20	V
I <sub>F</sub>	forward current	T <sub>sp</sub> ≤ 125 °C		-	2.83	А
I <sub>F(AV)</sub>	average forward current	δ < 0.5; f = 20 kHz; T <sub>sp</sub> ≤ 130 °C; square wave		-	2	A
		δ < 0.5; f = 20 kHz; T <sub>amb</sub> ≤ 65 °C; square wave	[1]	-	2	A
I <sub>FRM</sub>	repetitive peak forward current	t <sub>p</sub> = 1 ms; δ = 0.25		-	4	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	5	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	415	mW
			[3]	-	895	mW
			[1]	-	1565	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

### 9. Thermal characteristics

Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient	thermal resistance	in free air	[1][2]	-	-	300	K/W
	-		[1][3]	-	-	140	K/W
	ambient		[1][4]	-	-	80	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		[5]	-	-	20	K/W

 For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

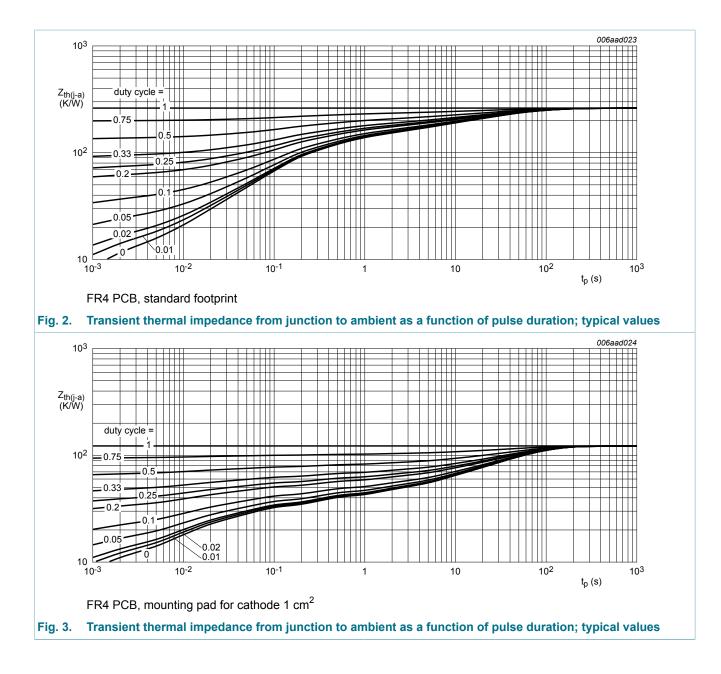
<sup>[3]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

[4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

[5] Soldering point of cathode tab.

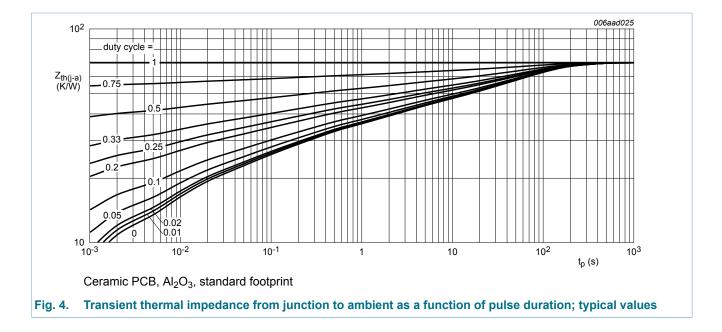
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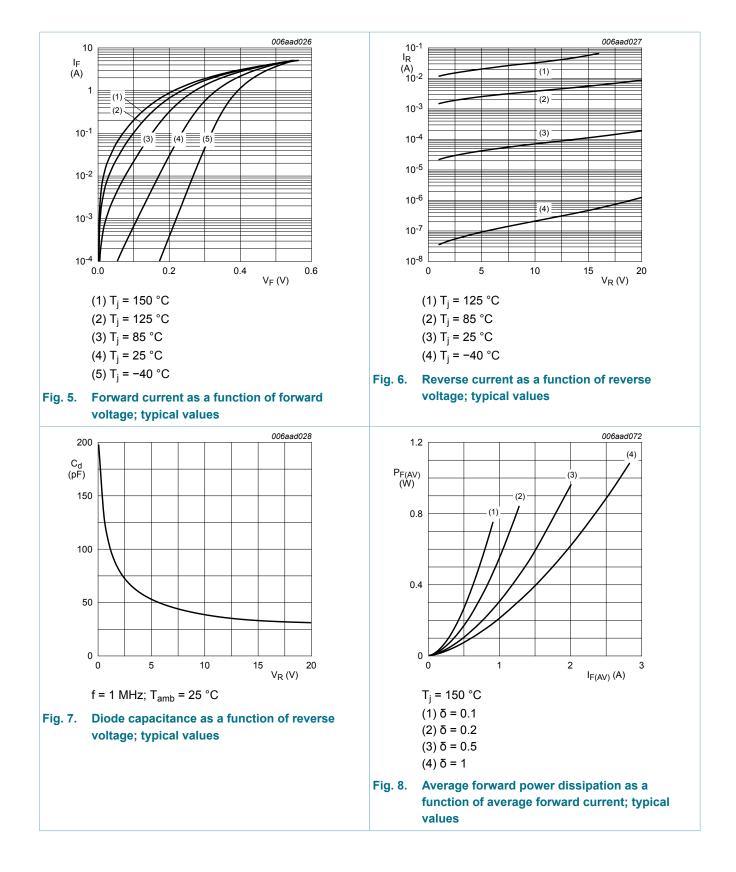


# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>F</sub> forward voltage	forward voltage	$I_F$ = 100 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>j</sub> = 25 °C	-	230	260	mV
	I <sub>F</sub> = 500 mA; pulsed; t <sub>p</sub> ≤ 300 μs; $\delta \le 0.02$ ; T <sub>j</sub> = 25 °C	-	290	330	mV	
	I <sub>F</sub> = 1 A; pulsed; t <sub>p</sub> ≤ 300 μs; $\delta$ ≤ 0.02; T <sub>j</sub> = 25 °C	-	330	380	mV	
		I <sub>F</sub> = 2 A; pulsed; t <sub>p</sub> ≤ 300 μs; $\delta$ ≤ 0.02; T <sub>j</sub> = 25 °C	-	395	450	mV
R reverse current	V <sub>R</sub> = 10 V; T <sub>j</sub> = 25 °C	-	70	350	μA	
		V <sub>R</sub> = 20 V; T <sub>j</sub> = 25 °C	-	220	900	μA
C <sub>d</sub> diode capacitance	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	105	120	pF
		V <sub>R</sub> = 10 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	40	50	pF
Dynamic cl	naracteristics					
t <sub>rr</sub>	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 \text{ °C}$	-	5	-	ns
V <sub>FRM</sub>	peak forward recovery voltage	$I_F = 0.5 \text{ A}; \text{ d}I_F/\text{d}t = 20 \text{ A}/\mu\text{s}; T_j = 25 \text{ °C}$	-	320	-	mV

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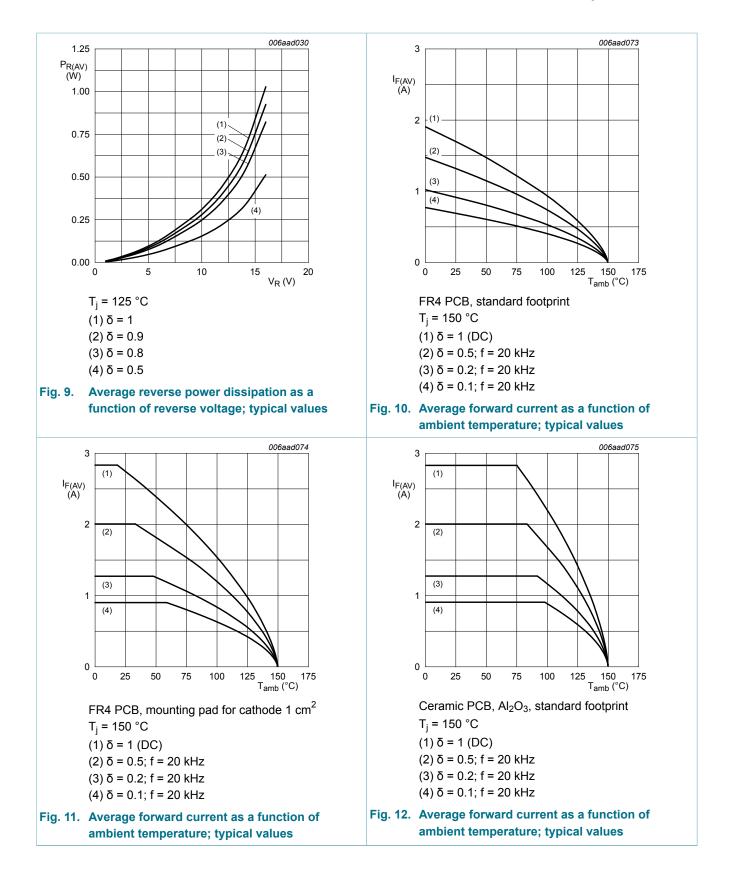
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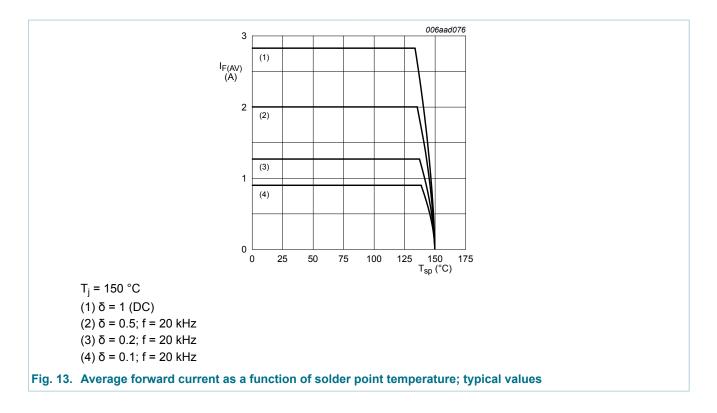
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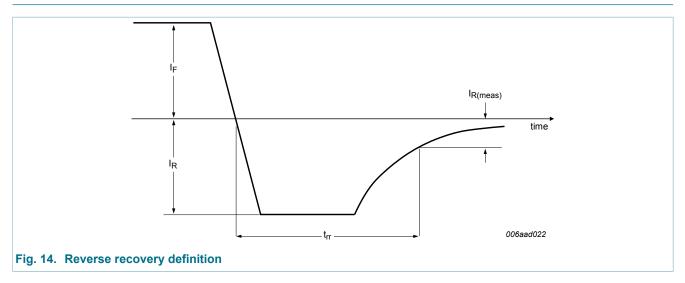


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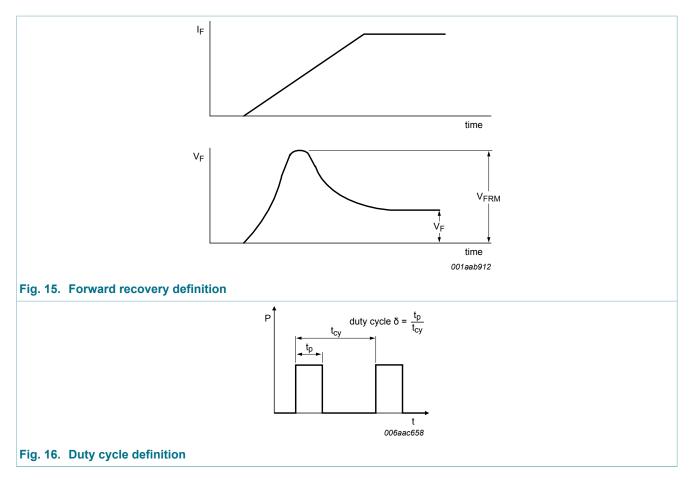


## **11. Test information**



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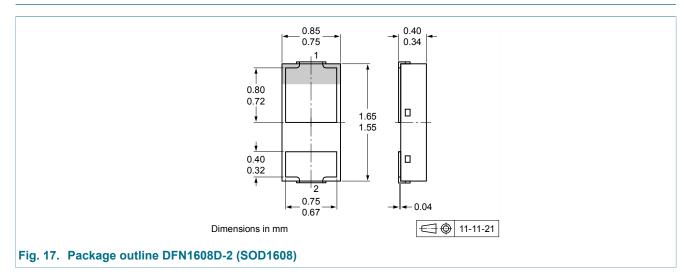
The current ratings for the typical waveforms are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

#### **11.1 Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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### 12. Package outline



## 13. Soldering

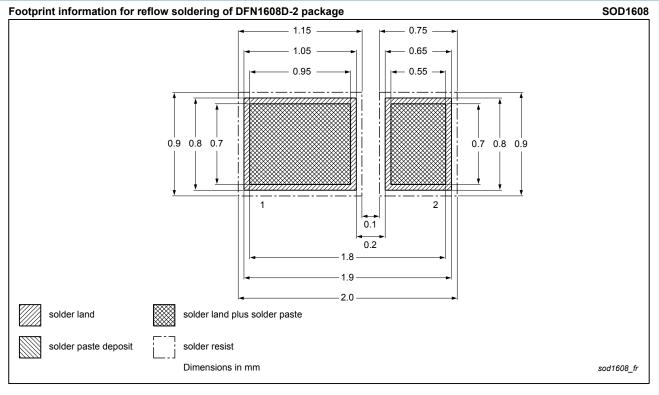


Fig. 18. Reflow soldering footprint for DFN1608D-2 (SOD1608)

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## 14. Revision history

Table 8. Revision hi	story			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG2020EPK v.2	20140210	Product data sheet	-	PMEG2020EPK v.1
Modifications:	Marking code corrected	•		
PMEG2020EPK v.1	20120425	Product data sheet	-	-

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### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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